

DMP1045U

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on) max}$	I_D $T_A = 25^\circ C$
-12V	31mΩ @ $V_{GS} = -4.5V$	5.2A
	45mΩ @ $V_{GS} = -2.5V$	4.3A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **ESD Protected Up To 3kV**
- **"Green" Device, Halogen and Antimony Free (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

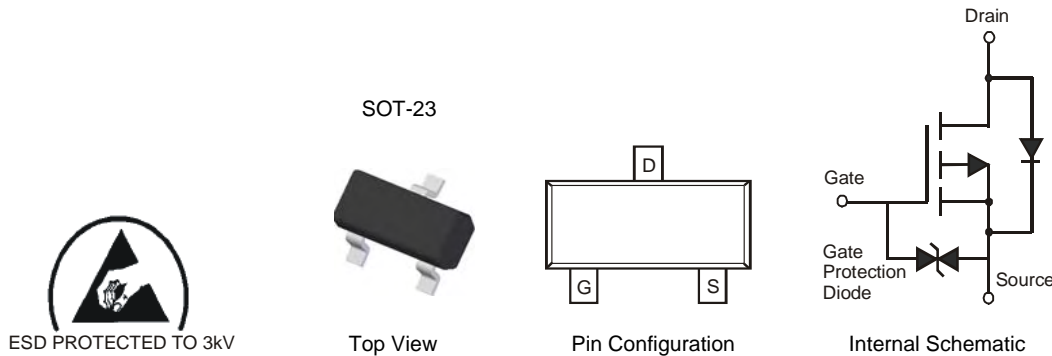
Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions
- Analog Switch

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0072 grams (approximate)

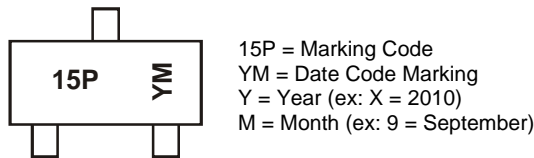


Ordering Information (Note 3)

Part Number	Case	Packaging
DMP1045U-7	SOT-23	3,000/Tape & Reel

Notes: 1. No purposefully added lead. Halogen and Antimony Free.

Marking Information



Date Code Key

Year	2010	2011	2012	2013	2014	2015
Code	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



DMP1045U

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 4) V _{GS} = -4.5V	Steady State	T _A = 25°C	I _D	4.0	A
		T _A = 70°C		3.1	
Continuous Drain Current (Note 4) V _{GS} = -2.5V	Steady State	T _A = 25°C	I _D	3.3	A
		T _A = 70°C		2.6	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = 25°C	I _D	5.2	A
		T _A = 70°C		4.2	
Continuous Drain Current (Note 5) V _{GS} = -2.5V	Steady State	T _A = 25°C	I _D	4.3	A
		T _A = 70°C		3.4	
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	2	A
Pulsed Drain Current (10us pulse, duty cycle=1%) (Note 4)			I _{DM}	40	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 4)	R _{θJA}	168	°C/W
Total Power Dissipation (Note 5)	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	99	°C/W
Thermal Resistance, Junction to Case (Note 5)	R _{θJc}	14.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	-1.0	μA	V _{DS} = -12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.3	-0.55	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	26	31	mΩ	V _{GS} = -4.5V, I _D = -4.0A
			31	45		V _{GS} = -2.5V, I _D = -3.5A
			45	75		V _{GS} = -1.8V, I _D = -2.7A
						V _{GS} = -1.8V, I _D = -2.7A
Forward Transfer Admittance	Y _{fs}	-	12	-	S	V _{DS} = -5V, I _D = -4A
Diode Forward Voltage	V _{SD}	-	-0.6	-	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	1357	-	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	-	504	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	235	-	pF	
Gate Resistnace	R _g	-	14.1	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 7)						
Total Gate Charge	Q _g	-	15.8	-	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4A
Gate-Source Charge	Q _{gs}	-	2.0	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.9	-	nC	
Turn-On Delay Time	t _{D(on)}	-	15.7	-	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 2.5Ω, R _G = 3.0Ω
Turn-On Rise Time	t _r	-	23.3	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	91.2	-	ns	
Turn-Off Fall Time	t _f	-	106.9	-	ns	

Notes: 2. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
3. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate